

Search History (6pp.) ~~11/17/05~~.. (11/17/05)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3844	((257/9) or (257/12) or (257/14) or (257/15) or (257/18) or (257/21) or (257/22) or (257/21) or (257/22) or (257/30) or (257/37) or (257/414) or (257/428) or (257/431) or (257/451)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/11/17 15:01
L2	0	1 and (infrared near3 ((photodiode) (photo adj detect\$3) photodetect\$3)).ti,ab, clm. and (MQW QW (quantum adj "well") QD QDs (quantum adj ("dots" "dot")))) and ("metal-insulator-semiconductor" MIS) near6 (quantum adj ("dot" "dots")) QD QDs)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:06
L3	31	1 and (infrared near3 ((photodiode) (photo adj detect\$3) photodetect\$3)).ti,ab, clm. and (MQW QW (quantum adj "well") QD QDs (quantum adj ("dots" "dot")))).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/17 15:06
S1	4	(infrared IR FIR) adj (photodetector photodetect\$3) and quantum and alumin\$um and ITO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 12:24
S2	1	((infrared IR FIR) adj (photodetector photodetect\$3) and quantum and alumin\$um and ITO).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/29 21:17
S3	2	("6268615").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 09:56
S4	3586	((257/9) or (257/12) or (257/14) or (257/15) or (257/18) or (257/21) or (257/22) or (257/30) or (257/37) or (257/414) or (257/428) or (257/431) or (257/451)).CCLS.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/05/30 09:57
S5	11	S4 and band adj gap near4 quantum adj dot	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 11:26

S6	0	wo-0211211\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 10:21
S7	1	wo-200211211\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 10:21
S8	10	"817113".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 10:37
S9	3	"817113".ap.	US-PGPUB	OR	OFF	2005/05/30 10:59
S10	4	S5 and barrier near4 InAs	US-PGPUB; USPAT	OR	OFF	2005/05/30 11:03
S11	2	S5 and barrier near4 InAs and quantum adj dot near4 InAs	US-PGPUB; USPAT	OR	OFF	2005/05/30 11:00
S12	2	S5 and barrier near4 InAs and quantum adj dot near8 InAs	US-PGPUB; USPAT	OR	OFF	2005/05/30 11:01
S13	2	S5 and barrier near4 InAs and quantum adj dot	USPAT	OR	ON	2005/05/30 11:02
S14	4	S5 and barrier near4 InAs	US-PGPUB; USPAT	OR	ON	2005/05/30 11:03
S15	5	(US-20040201009-\$.did. or (US-6268615-\$ or US-6885023-\$ or US-6720589-\$.did. or (WO-200211211-\$.did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/05/30 11:03
S16	0	S15 and barrier near4 InAs	US-PGPUB; USPAT	OR	ON	2005/05/30 11:03
S17	4	S4 and band adj gap near4 quantum adj dot and InAs near4 barrier	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 11:04
S18	2	band adj gap near6 quantum adj dot near6 ("low" "lower")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 11:50
S19	4	"6720589".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 11:31

S20	7	(US-20040201009-\$ or US-20050061986-\$).did. or (US-6268615-\$ or US-6885023-\$ or US-6720589-\$).did. or (WO-200211211-\$ or GB-2353635-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/05/30 11:48
S21	3	S20 and infrared	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 11:49
S22	0	S21 and band adj gap near6 quantum adj dot near6 ("low" "lower")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 11:50
S23	7	(US-20040201009-\$ or US-20050061986-\$).did. or (US-6268615-\$ or US-6885023-\$ or US-6720589-\$).did. or (WO-200211211-\$ or GB-2353635-\$).did.	US-PGPUB; USPAT; DERWENT	OR	OFF	2005/05/30 13:06
S24	0	S23 and polysilicon near6 (emitter collector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 13:07
S25	23	photodetector and polysilicon near6 (emitter collector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 13:12
S26	13	photodetector.ti,ab,clm. and polysilicon near6 (emitter collector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 13:24
S27	44	polysilicon near6 thermal adj budget	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 13:25
S28	0	polysilicon near6 thermal adj budget near6 cost	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 13:25
S29	0	polysilicon near6 thermal adj budget near6 amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 13:25

S30	0	polysilicon near6 thermal adj budget near6 amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 13:25
S31	30	polysilicon near6 thermal adj budget and amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 13:27
S32	0	polysilicon near6 thermal adj budget near20 amorphous	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 13:26
S33	1	polysilicon near6 thermal adj budget near6 advantage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 13:35
S34	0	emitter near8 (indium-tin-oxide ITO) and photodetector.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 13:36
S35	0	emitter near8 (indium-tin-oxide ITO) and photodetector.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 13:36
S36	137	emitter near8 (indium-tin-oxide ITO)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 13:37
S37	0	emitter near8 (indium-tin-oxide ITO) near10 (preventing prevent avoid avoiding)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 13:37
S38	2	emitter near8 (indium-tin-oxide ITO) near10 (reduce reduction reflect reflectance reflectivity preventing prevent avoid avoiding)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 14:03
S39	107	reticular adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/30 14:03

S40	9	(US-20040201009-\$ or US-20050061986-\$).did. or (US-6268615-\$ or US-6885023-\$ or US-6720589-\$ or US-5679960-\$).did. or (JP-2002198503-\$).did. or (WO-200211211-\$ or GB-2353635-\$).did.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/30 14:36
S41	1150	wetting adj layer	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/30 14:38
S42	487	wetting adj layer and semiconductor and "257"/\$7.ccls.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/30 14:38
S43	29	wetting adj layer and semiconductor and quantum adj dot and "257"/\$7.ccls.	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/30 14:41
S44	2	wetting adj layer and quantum adj dot near4 (Ge germanium)	US-PGPUB; USPAT; JPO; DERWENT	OR	OFF	2005/05/30 14:47
S45	36	stranski-krastanov and quantum adj dot	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/05/30 14:48
S46	6	stranski-krastanov and quantum adj dot and (Ge germanium) near6 (quantum adj dot)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/05/30 15:28
S47	53	("Si" near1 "O.sub."\$2 "SiO.sub.2" silicon adj oxide silicon adj dioxide) near4 (tunnel barrier) and photodetector	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/05/30 15:32
S48	53	("SiO.sub.2" silicon adj oxide silicon adj dioxide) near4 (tunnel barrier) and photodetector	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/05/30 16:08
S49	6	("SiO.sub.2" silicon adj oxide silicon adj dioxide) near4 (tunnel barrier) and photodetector and quantum adj dot	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/05/30 15:32
S50	3532	emitter near6 ((positive negative) adj voltage)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/05/30 16:08

S51	307	emitter near6 ((positive negative) adj voltage) and "257"/\$7.ccls. and circuit	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2005/05/30 16:09
S52	10	"817113".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/30 17:16
S53	10	"817113".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 13:12
S54	1	wo-200211211\$-\$\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 13:12
S55	2	("6885023").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 13:13
S56	1	S55 and spacer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/11/17 15:00